

D1
2. (Amended) An electrode structure including a conductive film formed on an insulation film without penetrating the insulation film, the insulation film being formed on a base substrate, the insulation film comprising a first film of polyimide having a plurality of openings which reach the base substrate, a second film formed on inside walls of the openings and formed of an insulation material having a higher hardness than polyimide, and a plurality of poles of polyimide buried in the openings with the second film formed on the inside walls thereof.

3. (Amended) A semiconductor light-emitting device having an electrode structure including a conductive film formed on an insulation film without penetrating the insulation film, the insulation film being formed on a base substrate, the insulation film comprising a plurality of poles of polyimide, a first film formed on side surfaces of the poles and formed of an insulation material having a higher hardness than polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on side surfaces thereof.

D2
5. (Amended) A semiconductor light-emitting device having an electrode structure including a conductive film formed on an insulating film without penetrating the insulation film, the insulation film being formed on a base substrate,

the insulation film comprising a first film of polyimide having a plurality of openings which reach the base substrate, a second film formed on inside walls of the openings and formed of an insulation material having a higher hardness than polyimide, and a plurality of poles of polyimide buried in the openings with the second film formed on the inside walls thereof.

D3
7. (Twice Amended) A semiconductor light-emitting device according to claim 3, wherein the conductive film is formed on a third film of an insulation material without penetrating the third film, the third film is formed on the insulation film.

8. (Twice Amended) A semiconductor light-emitting device according to claim 5, wherein the conductive film is formed on a third film of an insulation material without penetrating the third film, the third film is formed on the insulation film.

D4
13. (Twice Amended) A semiconductor light-emitting device including a waveguide, a lower electrode formed below the waveguide, and an upper electrode formed above the waveguide, the upper electrode having an electrode structure, the electrode structure including a conductive film formed on an insulation film without penetrating the insulation film, the insulation film being formed on a base substrate, the insulation film comprising a plurality of poles of polyimide, a first film formed on side surfaces of the poles and formed of an insulation material having a higher hardness than polyimide, and a second film of polyimide buried among said a plurality of poles with the first film formed on the side surfaces thereof.

14. (Twice Amended) A semiconductor light-emitting device including a waveguide, a lower electrode formed below the waveguide, and an upper electrode formed above the waveguide, the upper electrode having an electrode structure,

the electrode structure including a conductive film formed on an insulation film without penetrating the insulation film, the insulation film being formed on a base substrate,

the insulation film comprising a first film of polyimide having a plurality of openings a first film of polyimide having a plurality of openings which reach the base substrate, a second film formed on inside walls of the openings and formed of an insulation material having a higher hardness than polyimide, and a plurality of poles of polyimide buried in the openings with the second film formed on the inside walls thereof.
